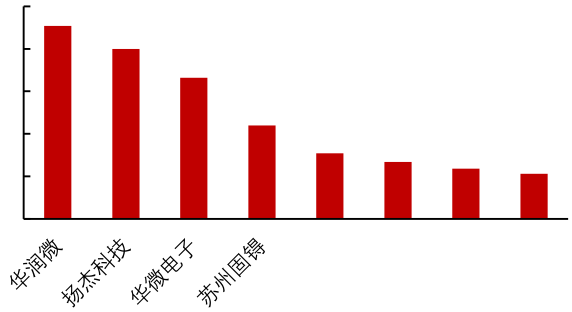
券

- MOSFET IGBT SJNFET /
  -100V 1500V MOSFET
  SiC/GaN
- 5
  2025 2019 70%
  /
  /
  13
- 50% 2017
  / MOSFET IGBT
  12
- 6 650V 1200V SiC JBS
  SiC JBS
  MOSFET GaN 650V
  MOCVD
- 2020-2022 0.83 1.07 1.25
  2021 72 PE 77
-

1. 券

1.1 IDM 度

6-8 5 2 1
20
MOSFET IGBT SJNFET / -100V 1500V
MOSFET SiC/GaN

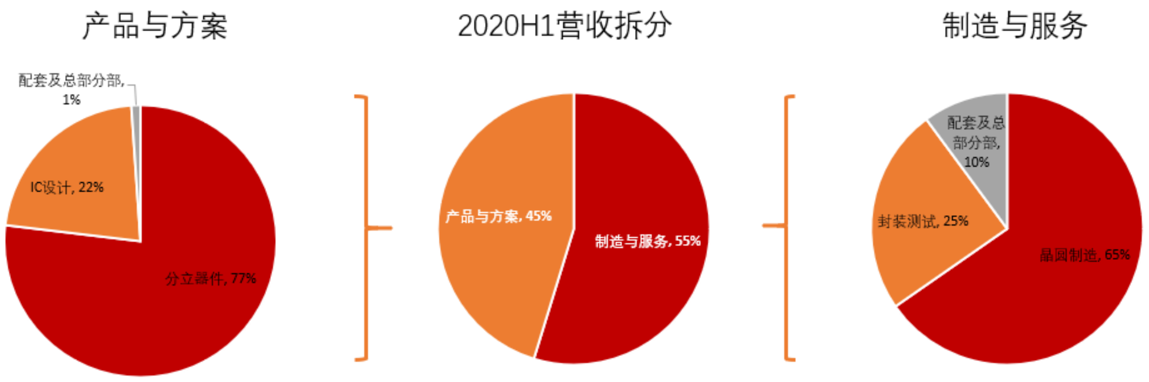


5-10

wind

下

2020 45% 55%
77%
65%



1.2 9 免

1983 4 1999

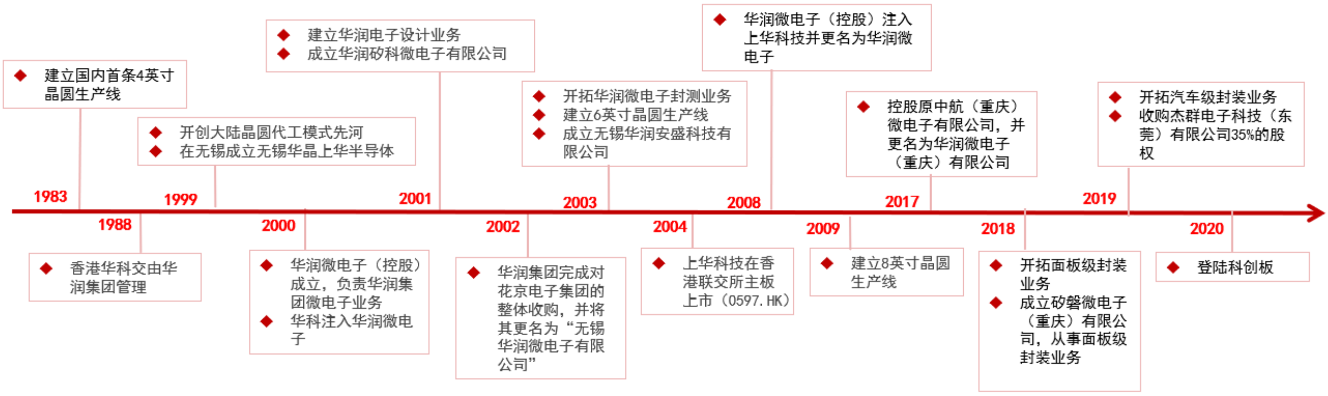
2001 2003 6

2004 0597.HK 2008

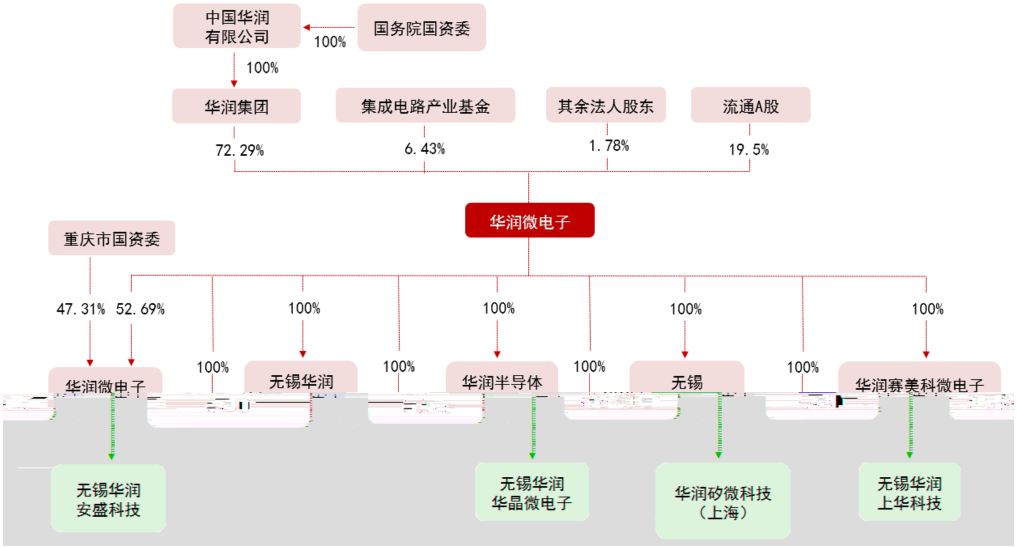
2009 8 2011 2017

2018 2019

2020



100%



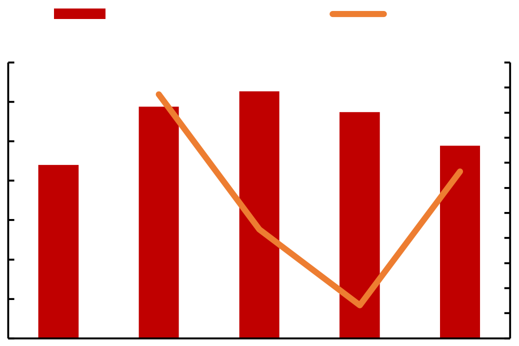
wind

1.3 境 券

2020 48.9 18.3%

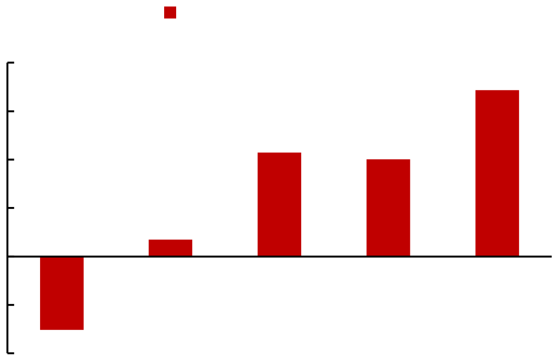
2019 2020

6.9 155%



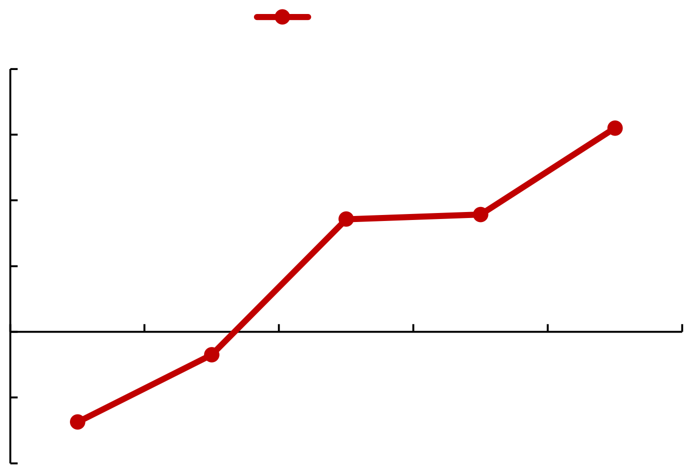
wind

建步 其



wind

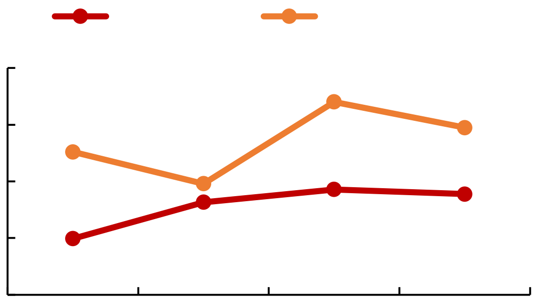
2016 2020 -6.9% 15.5%



wind

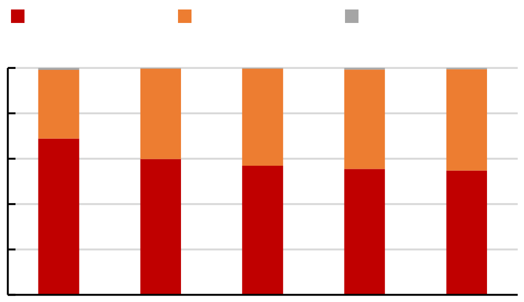
1 **IDM** IDM 30% 20% 10 IDM 2016 2020 IDM 30% 45% IDM

下 其



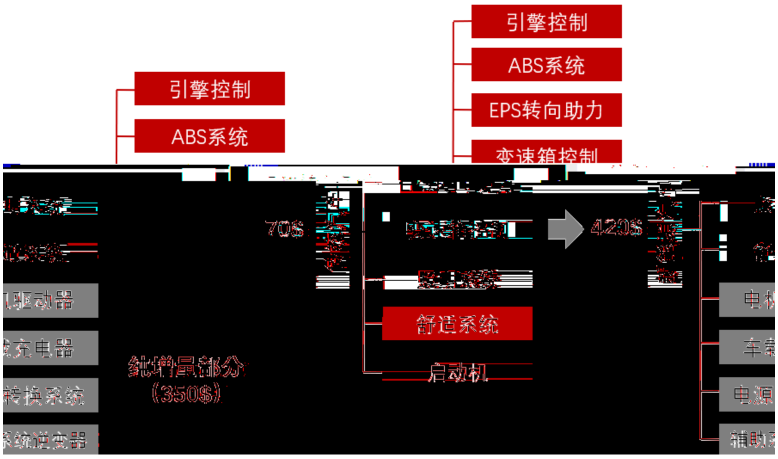
wind

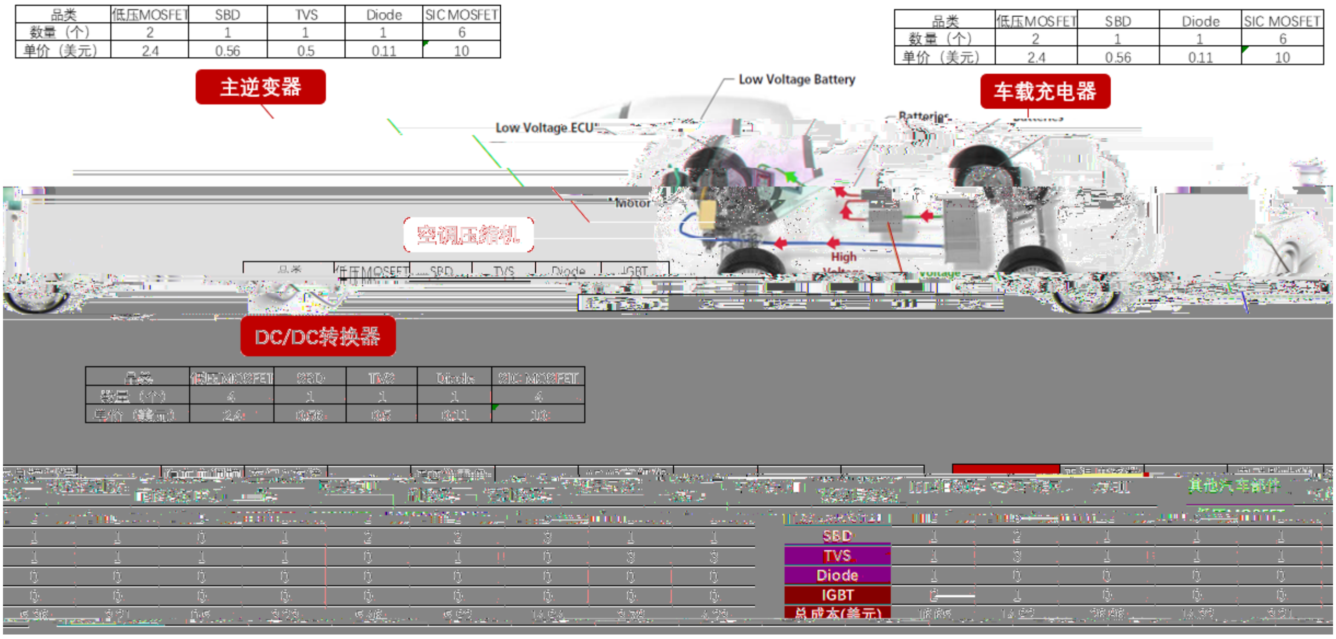
其



wind

望





品类	低压MOSFET	SBD	TVS	Diode	SIC MOSFET
数量（个）	2	1	1	1	6
单价（美元）	2.4	0.56	0.5	0.11	10

品类	低压MOSFET	SBD	Diode	SIC MOSFET
数量（个）	2	1	1	6
单价（美元）	2.4	0.56	0.11	10

品类	低压MOSFET	SBD	TVS	Diode	SIC MOSFET
数量（个）	4	1	1	1	4
单价（美元）	2.4	0.56	0.5	0.11	10

* SiC MOSFET IGBT

ROHM

5 Strategy Analytics

70 48V/MHEV-

90 HEV/PHEV- / 305 BEV- 350 5

上

数据来源：英飞凌

2019-2025 **70%** 2025 288

/ 2900 500 2025 271 2020 2025 CAGR 13%

- *I*

2 1/2
3

2021

24 他

EVTank

25 智 2021

MOSFET EVTank 2022 500 30% 50% 70% MOSFET 1.13 1.38 1.63 2019 2.7 3.1 3.5

26 MOSFET

* EVTank MOSFET EVTank

EVTank

2018 5

GB 17761-2018 2019 4 15

2018 2.5

90%

2.25 50% 2022-2024

4,000 7000 2019

55kg

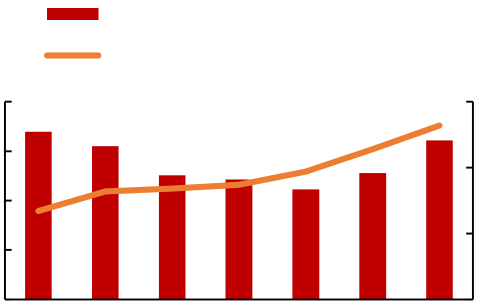
ZDC

2013 6.7% 2019 13.2%

MOSFET MOSFET

27

28 其



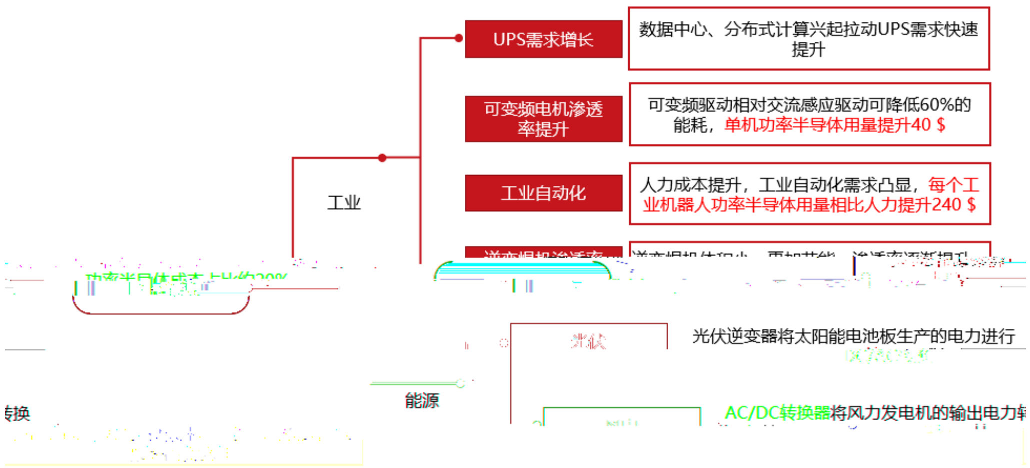
ZDC

➢ /

40

/ 240 / AC/DC DC/AC

券



数据来源：

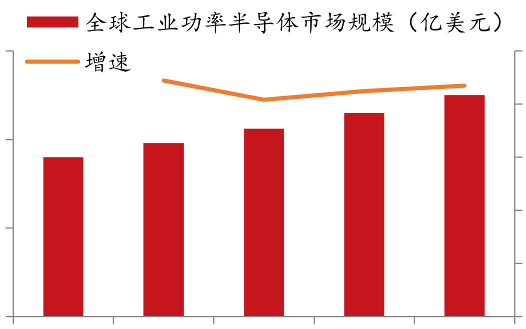
20-22 CAGR 8% 2019

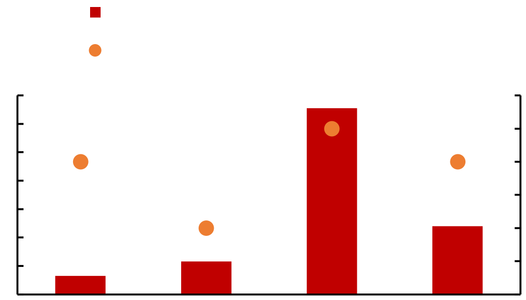
115 2020 125 9%

UPS

13 23 131 48 215

3 20-22 CAGR 8%

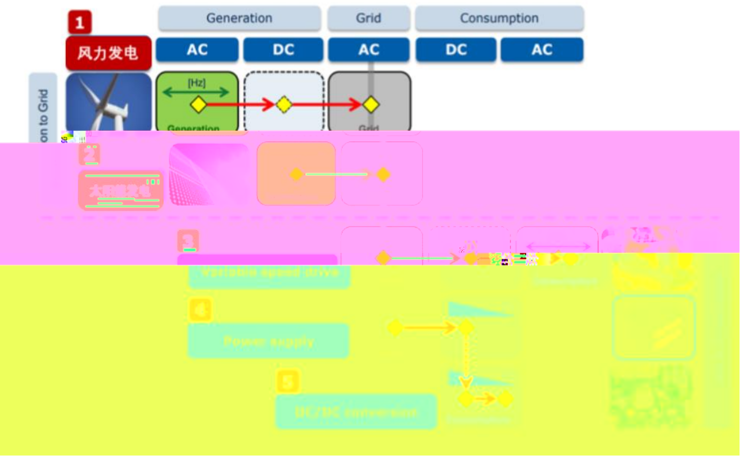




* UPS 20% 20%
26.5% 19%

AC/DC

DC/AC



数据来源：英飞凌、

50

2018 36%

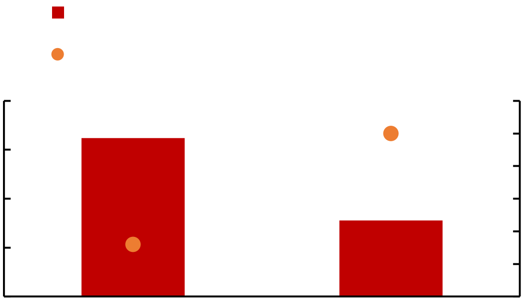
2019-

2023 124GW 20GW

30 2018 25%

2022 385GW

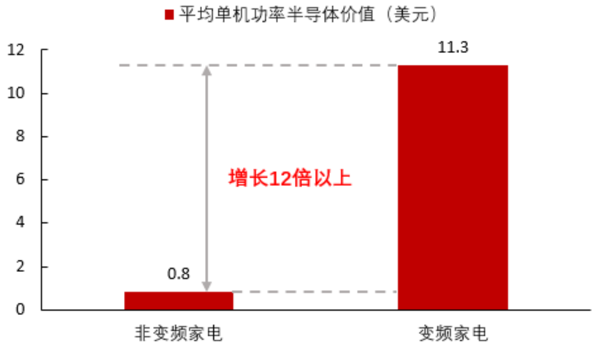
2022 20 19-22 CAGR 10%

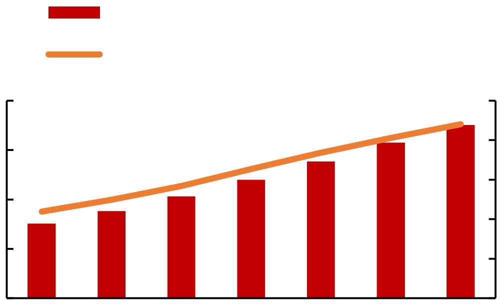


* 0.13 /W 0.2 /W 1 /MW

2.45 /MW

15%-30%
10 20 20%
2019 57% 2023 88% IPM MOSFET
IGBT 12
2019 41 2023 70 4
CAGR 14%

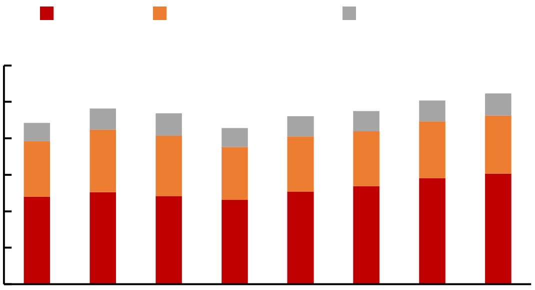




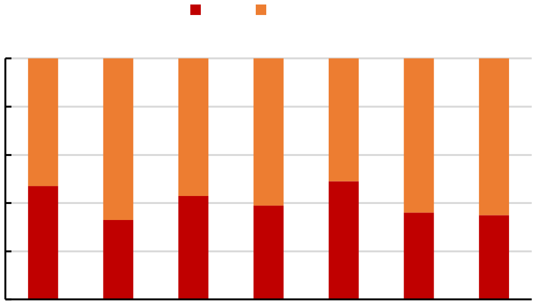
2.3

50% Omida 2019
468 36% IHS
2017 50%
IGBT MOSFET 30%

取 其



Omdia



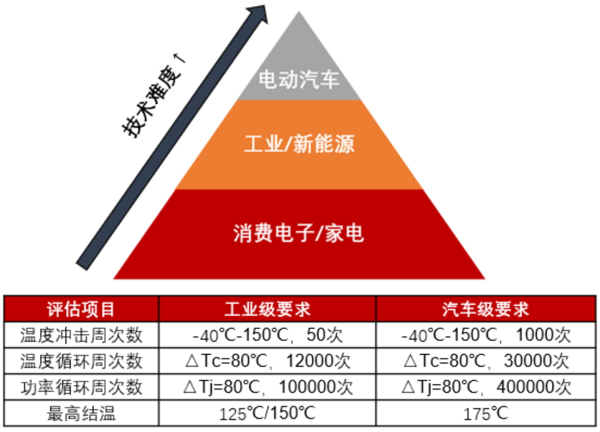
Yole

10

MOSFET 2016

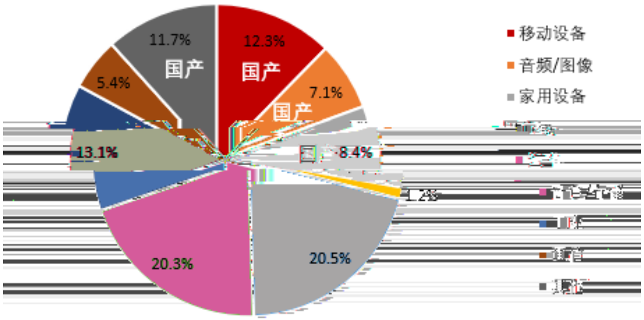
/

取



评估项目	工业级要求	汽车级要求
温度冲击周次数	-40℃-150℃，50次	-40℃-150℃，1000次
温度循环周次数	△Tc=80℃，12000次	△Tc=80℃，30000次
功率循环周次数	△Tj=80℃，100000次	△Tj=80℃，400000次
最高结温	125℃/150℃	175℃

其



3.

3.1 所 他

MOSFET IGBT SJNFET /

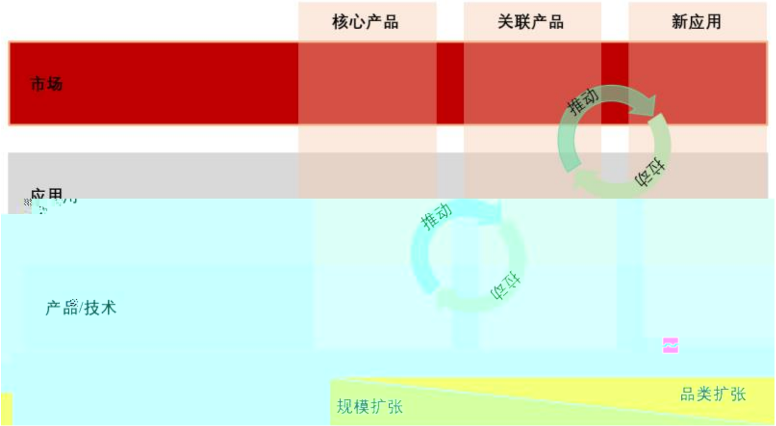
MOSFET -100V
1500V MOSFET MOSFET
MOS VDMOS
MOS MOSFET

—

IGBT 20 80 IGBT 6
PT FS-Trench
600V 6500V
IGBT
IGBT

所

IC MOSFET IGBT
8 Trench
FRD
IC BCD
IC IC IC
IC LED IC IC



1 2
3

➢

MOS MOS MOS
2.2 5000 OBC/

/ IGBT IGBT 2020
50% 6000 IGBT

2020 7 4 1200V
650V SiC 6 SiC

智

➢

GaN **IC** 2.44
650V
650V MOCVD
GaN IP
GaN GaN
IC IC

所

智

56.2%

2019 IPM

500V 5A IPM 600V 15A

IPM

7 10 PT6007B PT6010

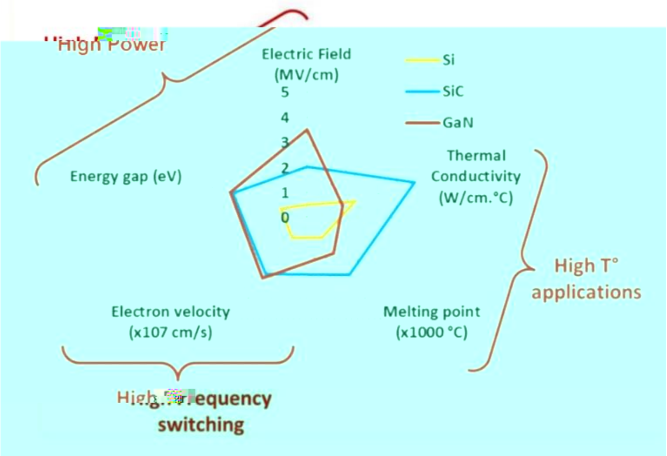
3.3 智

BCD MEMS

技术	BCD	HV CMOS	Mixed-Signal	Logic/RF	e-NVM
0.13um/0.11um	○			●	○
0.18um/0.153um	●	●	●	●	●
0.25um			●		
0.35pm			●		
0.5um	●	●	●	●	●
>0.5um	●	●	●	●	
>1.0um		●	●	●	
MEMS	压力传感器。有 MIGrophone 传感器和 Photoele MEMS。 陀螺仪和加速度计正在开发中。				
Power Discrete	包括平面 DMOS、Trench DMOS、IGBT、FRD、双极晶体管。IGBT 3300V 6500V 正在开发中。				

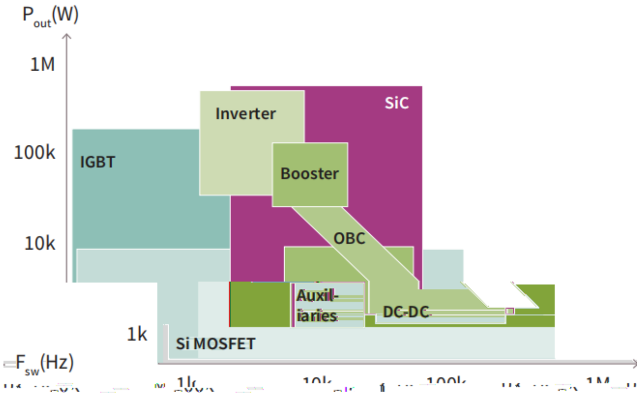
●表示可获得 ○表示开发中

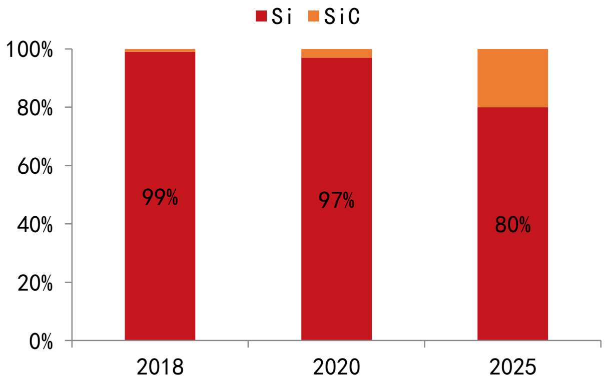
变



数据来源：

SiC **Si** SiC
DC/AC DC/DC OBC DC/AC
SiC Si
SiC 6kg 43%
75% SiC 3% 2025
20% 6

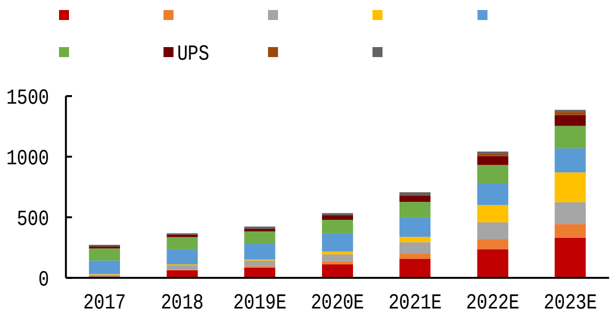




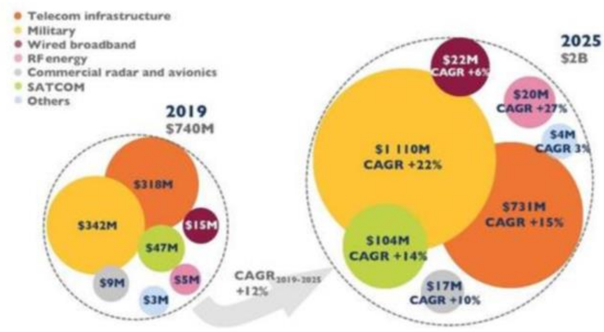
GaN
GaN IC
SiC **GaN** Yole
SiC 2018 3.7 2023 14 CAGR

30% GaN
12%

2019 7.4 2025 20 CAGR



Yole



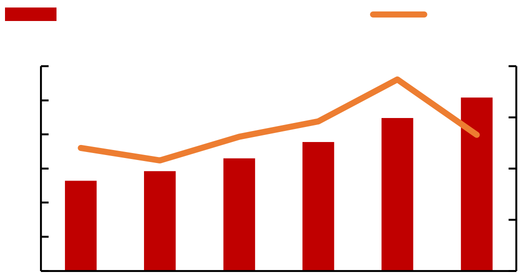
Yole

SiC GaN SiC GaN 1.42 2.44 6 650V 1200V SiC JBS SiC JBS MOSFET GaN 650V MOCVD SiC GaN

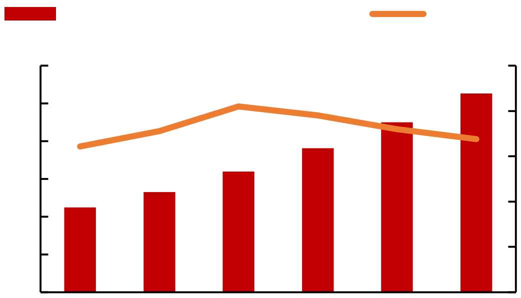
4.2

Yole 2019 MEMS 165 10%

2019 90 50%
MEMS 40%



Yole



MEMS
MEMS 8
6
MEMS 6 8
2019

下

4.3 所 厂

62

PEP INNOVATION
5.5

下

2020H1 1.27 35%

50

38 42

5G

AIOT

应

2020-2022

1)

2) 5G

20-22

22.7% 23.3% 23.7%

20-22 35.1% 35.7%

35.8%

20-22 28.3% 29.4% 30.2%

3) 20-22 1.64% 1.63% 1.58%

5.34% 5.3% 5.2% 20-22

7.36% 7.31% 7.26%.

4) 20-22 3%

	2018A	2019A	2020E	2021E	2022E
	6,270.8	**5,742.8**	**6,887.9**	**7,935.6**	**8,892.8**

应

2020-2022 0.83 1.07 1.25

IDM MOSFET IGBT

\+ IGBT IDM MOSFET

2021 72 PE 77

1

MOSFET MOSFET IGBT

2

3

4

10%

信

:	2018A	2019A	2020E	2021E	2022E
	1,538	1,931	8,353	9,295	10,022

:	2018A	2019A	2020E	2021E	2022E
	6,271	**5,743**	**6,888**	**7,936**	**8,893**

12 /

15%

5% 15%

-5% +5%

-5%

5%

-5% +5%

-5%